

NGTB75N60FL2WG-VB Datasheet

600V Trench and Fieldstop IGBT

PRODUCT SUMMARY		
V _{CE} (V)	600	
I _C (A)	90 (T _C =25 °C)	75 (T _C =100 °C)
V _{CE (sat)} (V)	1.7	
Q _g (nC)	175	
I _{CM} (A)	225	

FEATURES

- Very Low V_{CEsat}
- Low turn-off losses
- High speed switching
- Maximum junction temperature 175°C
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)



RoHS
COMPLIANT
HALOGEN
FREE

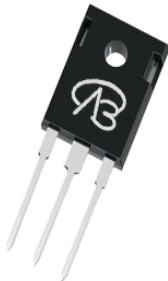
APPLICATIONS

- Telecommunications
 - Server and telecom power supplies
- Lighting
 - High-intensity discharge (HID)
 - Fluorescent ballast lighting
- Consumer and computing
 - ATX power supplies
- Industrial
 - Welding
 - Battery chargers
- Renewable energy
 - Solar (PV inverters)
- Switch mode power supplies (SMPS)

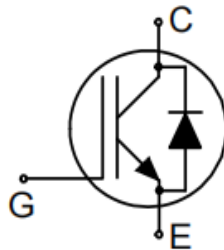
Package pin definition

- Pin1 G - Gate
- Pin2 C & backside - Collector
- Pin3 E - Emitter

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Top View



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)			
PARAMETER	SYMBOL	LIMIT	UNIT
Collector-Emitter Voltage	V _{CE}	600	V
Gate-Emitter Voltage	V _{GE}	±30	
Continuous Collector Current (T _J = 150 °C)	V _{GE} at 15 V	T _C = 25 °C	150
		T _C = 100 °C	75
Pulsed Collector Current ^a	I _{CM}	225	A
Diode Forward Current ^b	I _F	90	A
Maximum Power Dissipation	P _D	T _C = 25 °C	400
		T _C = 100 °C	220
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +175	°C
Short Circuit Withstand Time ^{TC=150}	t _{sc}	V _{GE} = 15V, V _{CE} 400V	3
Short Circuit Withstand Time ^{TC=100}		V _{GE} = 15V, V _{CE} 330V	5
Soldering Recommendations (Peak Temperature) ^c		for 10 s	260
			°C

Notes

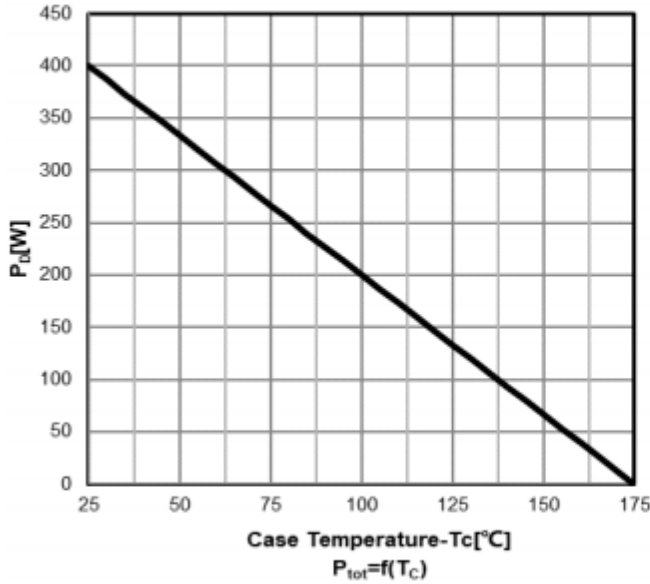
- Repetitive rating; pulse width limited by maximum junction temperature.
- Current limited by maximum junction temperature.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case	R_{thJC}	-	0.5	

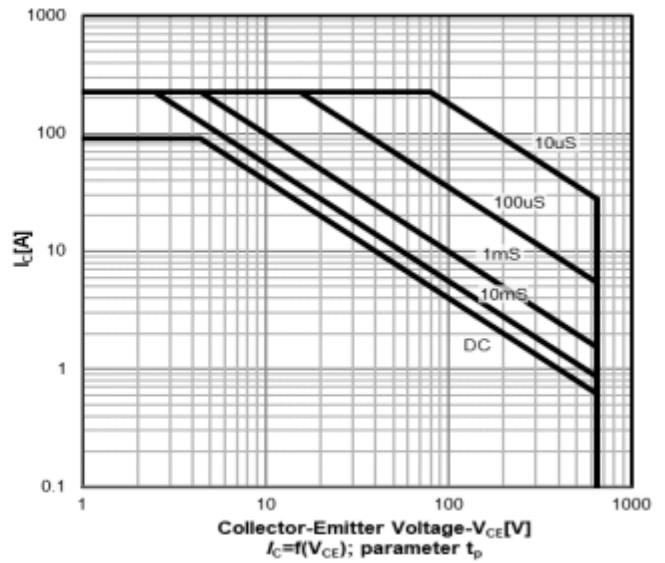
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Collector-Emitter Breakdown Voltage	BV_{CE}	$V_{GE} = 0\text{ V}, I_C = 250\text{ }\mu\text{A}$ $V_{GE} = 0\text{ V}, I_C = 1\text{ mA}$		600 600	- -	- -	V
Gate-Source Threshold Voltage (N)	$V_{GE(th)}$	$V_{CE} = V_{GE}, I_D = 250\text{ }\mu\text{A}$		4	5	6	V
Zero Gate Voltage Collector Current	I_{CES}	$V_{CE} = 480\text{ V}, V_{GE} = 0\text{ V}, T_J = 25\text{ }^\circ\text{C}$		-	1	20	μA
		$V_{CE} = 480\text{ V}, V_{GE} = 0\text{ V}, T_J = 150\text{ }^\circ\text{C}$		-	1000	-	μA
Gate-Emitter Leakage Current	I_{GES}	$V_{CE} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	100	nA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$V_{GE} = 15\text{ V}$	$I_C = 75\text{ A}$	-	1.7	2.1	V
Forward Transconductance	g_{fs}	$V_{CE} = 20\text{ V}, I_C = 75\text{ A}$		-	40	-	S
Dynamic							
Input Capacitance	C_{ies}	$V_{GE} = 0\text{ V}, V_{CE} = 25\text{ V},$ $f = 500\text{ KHz}$		-	4600	-	pF
Output Capacitance	C_{oes}			-	235	-	
Reverse Transfer Capacitance	C_{res}			-	72	-	
Turn-on Energy	E_{on}	$V_{CE} = 400\text{ V}, V_{GE} = 0/15\text{V},$ $I_C = 75\text{ A}, R_g = 10\text{ }\Omega$		-	0.62	-	ns
Turn-off Energy	E_{off}			-	0.31	-	
Total Gate Charge	Q_g	$V_{GE} = 15\text{ V}$	$I_C = 75\text{ A}, V_{CE} = 400\text{ V}$	-	175	-	nC
Gate-Emitter Charge	Q_{ge}			-	14	-	
Gate to Collector Charge	Q_{gc}			-	33	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{CE} = 400\text{ V}, V_{GE} = 0/15\text{V},$ $I_C = 75\text{ A}, R_g = 10\text{ }\Omega$		-	60	-	ns
Rise Time	t_r			-	43	-	
Turn-Off Delay Time	$t_{d(off)}$			-	184	-	
Fall Time	t_f			-	30	-	
Internal emitter inductance measured 5 mm	L_E			-	13	-	
Diode Characteristics							
Diode Forward Current	I_F	IGBT symbol showing the integral reverse junction diode		-	-	75	A
Pulsed Diode Forward Current	I_{FM}			-	-	225	
Diode Forward Voltage	V_F	$I_F = 30\text{ A}$		-	1.65	2.0	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 30\text{ A},$ $di/dt = 200\text{ A}/\mu\text{s}, V_R = 400\text{ V}$		-	73	-	ns
Reverse Recovery Charge	Q_{rr}			-	85	-	μC
Reverse Recovery Current	I_{RRM}			-	13	-	A

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

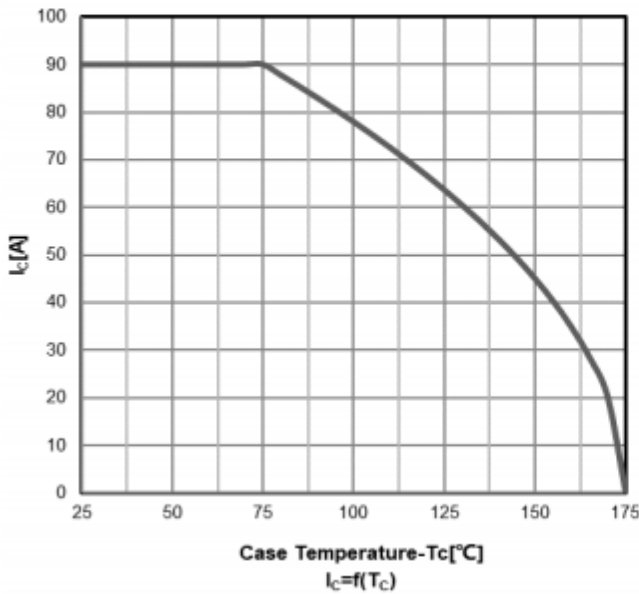
Power dissipation



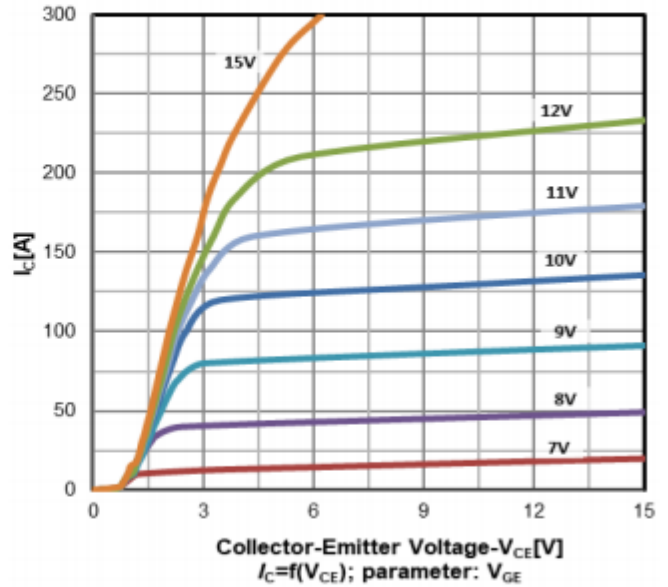
Safe operating area $T_a=25\text{ °C}$



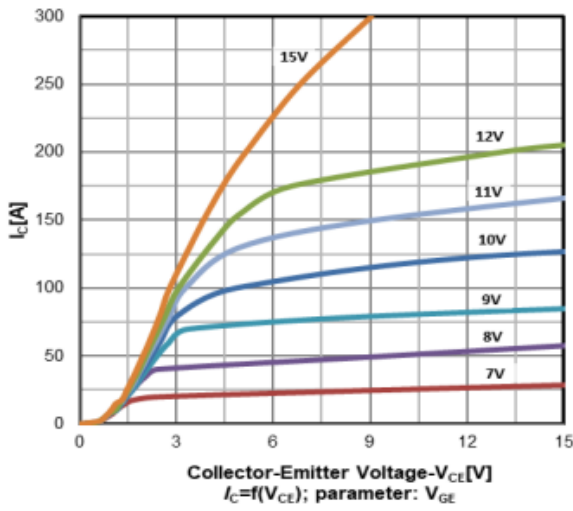
Collector current as a function of Case temperature



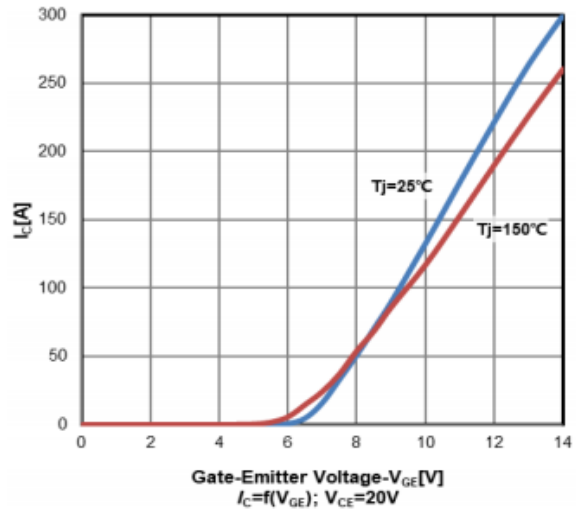
Typ. Output characteristics $T_j=25\text{ °C}$



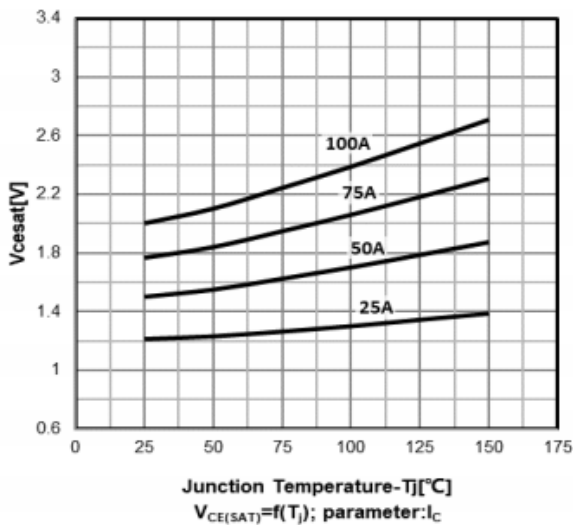
Typ. Output characteristics
 $T_j=150\text{ }^\circ\text{C}$



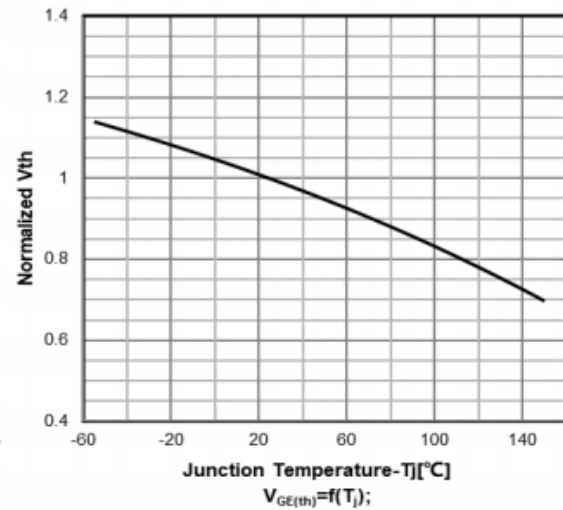
Typ. Transfer characteristics



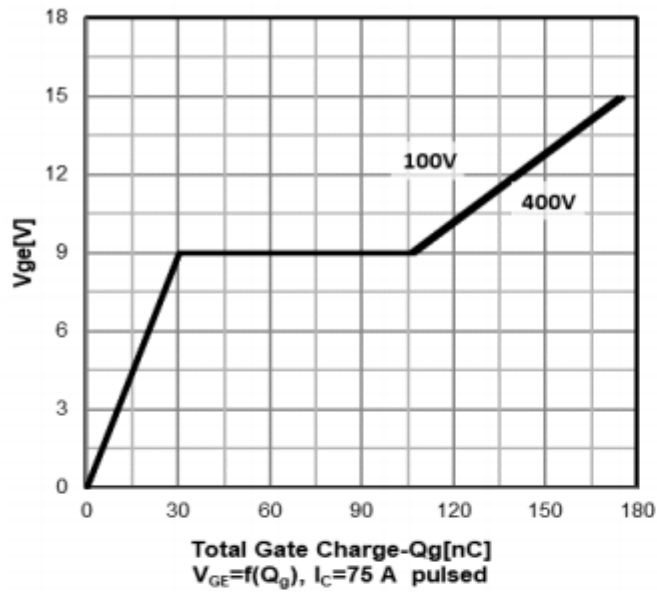
Typ. Collector-emitter saturation voltage as a function of junction temperature ($V_{GE}=15\text{V}$)



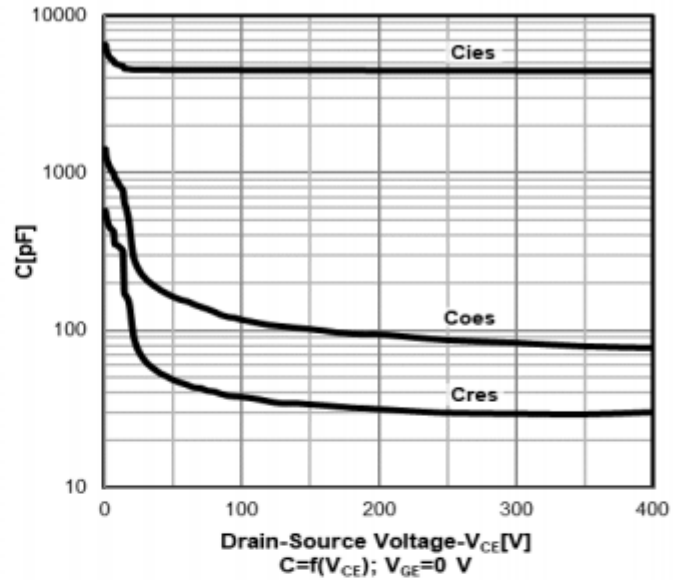
Normalized $V_{GE(th)}$ vs. temperature



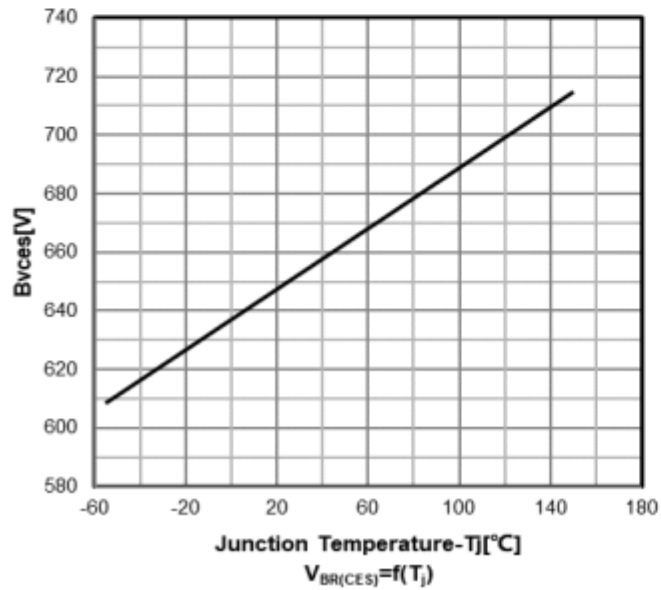
Gate charge characteristics



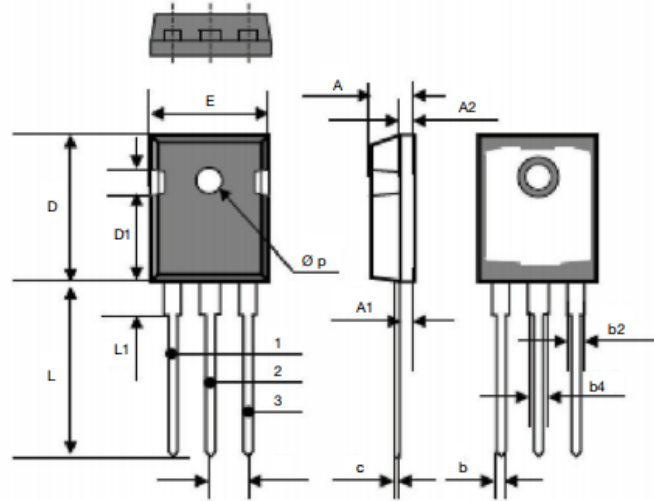
Capacitance characteristics



Collector-emitter breakdown voltage vs. temperature



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DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.70	5.31	0.185	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b2	1.65	2.41	0.065	0.095
b4	2.59	3.43	0.102	0.135
c	0.61 BSC		0.024 BSC	
D	20.80	21.46	0.819	0.845
D1	3.68	5.49	0.145	0.216
(e)	5.46 BSC		0.215 BSC	
E	15.49	16.26	0.610	0.640
L	19.81	20.32	0.780	0.800
L1	4.06	4.50	0.160	0.177
$\varnothing p$	3.51	3.66	0.138	0.144

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